

HM10490 Series

65536-Words × 1-Bit Fully Decoded Random Access Memory

DESCRIPTION

The HM10490 is ECL 10K compatible, 65536-words by 1-bit read/write random access memory developed for high speed systems such as scratch pads and control/buffer storage.

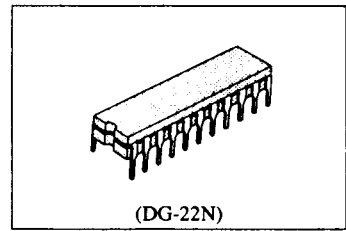
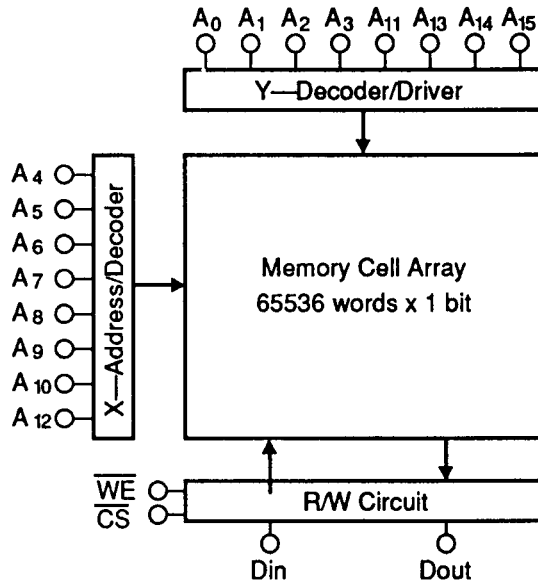
FEATURES

- 65536 × 1 Bit Organization
- Fully Compatible with 10K ECL Level
- Address Access Time10/12ns (max.)
- Write Pulse Width6/8ns (min.)
- Low Power Dissipation570mW (typ.)
- Output Obtainable by Wired-OR (Open Emitter)

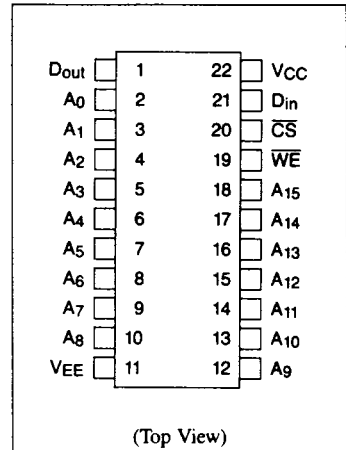
ORDERING INFORMATION

Type No.	Access Time	Package
HM10490-10	10ns	300 mil 22 pin Cerdip
HM10490-12	12ns	(DG-22N)

BLOCK DIAGRAM



PIN ARRANGEMENT



FUNCTION TABLE

Input			Output	Mode
\overline{CS}	\overline{WE}	D_{in}		
H	X	X	L	Not Selected
L	L	L	L	Write "0"
L	L	H	L	Write "1"
L	H	X	D_{out}^*	Read

NOTES: X = Irrelevant;
* = Read out noninvert

■ ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

Item	Symbol	Rating	Unit
Supply Voltage	V_{EE} to V_{CC}	+0.5 to Θ 7.0	V
Input Voltage	V_{in}	+0.5 to V_{EE}	V
Output Current	I_{out}	Θ 30	mA
Storage Temperature	T_{stg}	Θ 65 to +150	$^\circ\text{C}$
Storage Temperature	$T_{stg(bias)}$ *	Θ 55 to +125	$^\circ\text{C}$

NOTE: * = Under bias.

■ DC CHARACTERISTICS ($V_{EE} = \Theta 5.2\text{V}$, $R_L = 50\Omega$ to $\Theta 2.0\text{V}$, $T_a = 0$ to $+75^\circ\text{C}$, air flow exceeding 2m/sec.)

Item	Symbol	Test Condition	Min.(B)	Typ.	Max.(A)	Unit			
Output Voltage	V_{OH}	$V_{in} = V_{IHA}$ or V_{ILB}	0°C	Θ 1000	—	Θ 840	mV		
			$+25^\circ\text{C}$	Θ 960	—	Θ 810			
			$+75^\circ\text{C}$	Θ 900	—	Θ 720			
	V_{OL}		0°C	Θ 1870	—	Θ 1665			
			$+25^\circ\text{C}$	Θ 1850	—	Θ 1650			
			$+75^\circ\text{C}$	Θ 1830	—	Θ 1625			
Output Threshold Voltage	V_{OHC}	$V_{in} = V_{IHB}$ or V_{ILA}	0°C	Θ 1020	—	—	mV		
			$+25^\circ\text{C}$	Θ 980	—	—			
			$+75^\circ\text{C}$	Θ 920	—	—			
	V_{OLC}		0°C	—	—	Θ 1645			
			$+25^\circ\text{C}$	—	—	Θ 1630			
			$+75^\circ\text{C}$	—	—	Θ 1605			
Input Voltage	V_{IH}	Guaranteed Input Voltage High for All Inputs	0°C	Θ 1145	—	Θ 840	mV		
			$+25^\circ\text{C}$	Θ 1105	—	Θ 810			
			$+75^\circ\text{C}$	Θ 1045	—	Θ 720			
	V_{IL}		0°C	Θ 1870	—	Θ 1490			
			$+25^\circ\text{C}$	Θ 1850	—	Θ 1475			
			$+75^\circ\text{C}$	Θ 1830	—	Θ 1450			
Input Current	I_{IH}	$V_{in} = V_{IHA}$	0 to $+75^\circ\text{C}$	—	—	220	μA		
				I_{IL}	$V_{in} = V_{ILB}$	CS		0.5	—
	Others							Θ 50	—
Supply Current	I_{EE}	All Inputs and Outputs Open	0°C , 75°C	Θ 140	—	—	mA		

■ AC CHARACTERISTICS ($V_{EE} = \Theta 5.2\text{V} \pm 5\%$, $T_a = 0$ to $+75^\circ\text{C}$, air flow exceeding 2m/sec.)

1. Read Mode

Item	Symbol	Test Condition	HM10490-10			HM10490-12			Unit
			Min.	Typ.	Max.	Min.	Typ.	Max.	
Chip Select Access Time	t_{ACS}		—	—	6	—	—	8	ns
Chip Select Recovery Time	t_{RCS}		—	—	6	—	—	8	ns
Address Access Time	t_{AA}		—	—	10	—	—	12	ns

2. Write Mode

Item	Symbol	Test Condition	Min.	Typ.	Max.	Min.	Typ.	Max.	Unit
Write Pulse Width	t_w	$t_{WSA} = t_{WSA} \text{ min.}$	6	—	—	8	—	—	ns
Data Setup Time	t_{WSD}		2	—	—	2	—	—	ns
Data Hold Time	t_{WHD}		2	—	—	2	—	—	ns
Address Setup Time	t_{WSA}	$t_w = t_w \text{ min.}$	2	—	—	2	—	—	ns
Address Hold Time	t_{WHA}		2	—	—	2	—	—	ns
Chip Select Setup Time	t_{WSCS}		2	—	—	2	—	—	ns
Chip Select Hold Time	t_{WHCS}		2	—	—	2	—	—	ns
Write Disable Time	t_{WS}		—	—	6	—	—	8	ns
Write Recovery Time	t_{WR}		—	—	12	—	—	14	ns

3. Rise/Fall Time

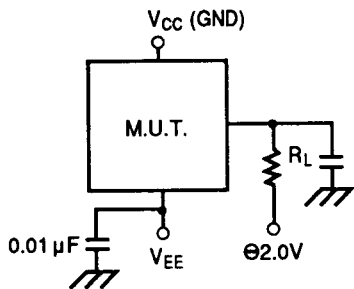
Item	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Output Rise Time	t_r		—	2	—	ns
Output Fall Time	t_f		—	2	—	ns

4. Capacitance

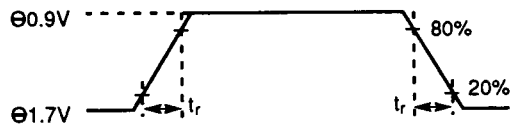
Item	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Input Capacitance	C_{in}		—	3	—	pF
Output Capacitance	C_{out}		—	5	—	pF

■ TEST CIRCUIT AND WAVEFORMS

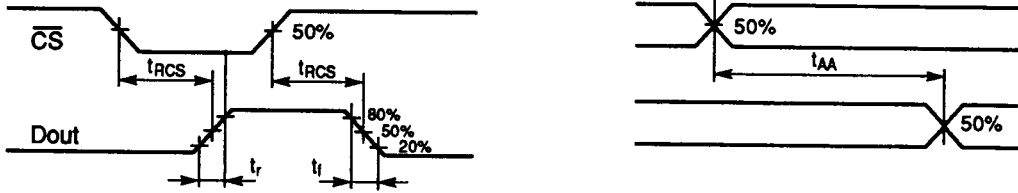
1. Loading Condition



2. Input Pulse



3. Read Mode



4. Write Mode

